

# PMCM6501UNEZ Datasheet



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DiGi Electronics Part Number PMCM6501UNEZ-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PMCM6501UNEZ

Description MOSFET N-CH 20V 8.7A 6WLCSP

Detailed Description N-Channel 20 V 8.7A (Ta) 400mW Surface Mount 6-

WLCSP (1.48x0.98)



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# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
PMCM6501UNEZ	Nexperia USA Inc.
Series:	Product Status:
-	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
20 V	8.7A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
1.5V, 4.5V	21mOhm @ 3A, 4.5V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
900mV @ 250μA	6.2 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±8V	1050 pF @ 10 V
FET Feature:	Power Dissipation (Max):
	400mW
Operating Temperature:	Mounting Type:
150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
6-WLCSP (1.48x0.98)	6-XFBGA, WLCSP
Base Product Number:	
PMCM6501	

# **Environmental & Export classification**

8541.21.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	

**Product data sheet** 

### 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a 6 bumps Wafer Level Chip-Size Package (WLCSP) using Trench MOSFET technology.

#### 2. Features and benefits

- Low threshold voltage
- Ultra small package: 0.98 × 1.48 × 0.35 mm
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

### 3. Applications

- · Relay driver
- · High-speed line driver
- Low-side loadswitch
- · Switching circuits

#### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	20	V
$V_{GS}$	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	8.7	Α
Static characte	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 3 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	17	21	mΩ

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>



# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
A1	G	gate	1 2	D
A2	S	source	A	
B1	S	source	B	G $\downarrow$ $\downarrow$ $\downarrow$
B2	S	source		
C1	D	drain		
C2	D	drain	Transparent top view WLCSP6 (WLCSP6_3-2)	S 017aaa255

# 6. Ordering information

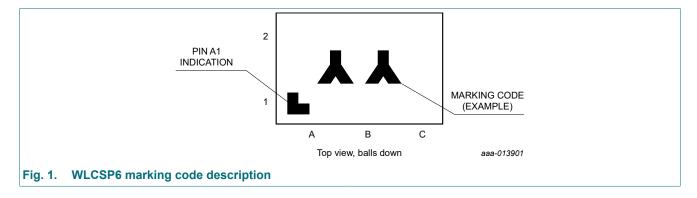
**Table 3. Ordering information** 

Type number	Package	<sup>2</sup> ackage					
	Name	Description	Version				
PMCM6501UNE	WLCSP6	wafer level chip-size package; 6 bumps (3 x 2)	WLCSP6_3-2				

### 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PMCM6501UNE	AE



# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	20	V
$V_{GS}$	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	8.7	Α
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	6.6	Α
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	4.2	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	27	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	556	mW
			[1]	-	1.3	W
		T <sub>sp</sub> = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source Drai	n Diode					
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.2	Α

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper; tin-plated and standard footprint.

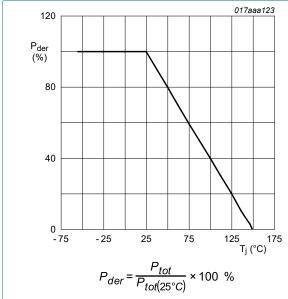


Fig. 2. Normalized total power dissipation as a function of junction temperature

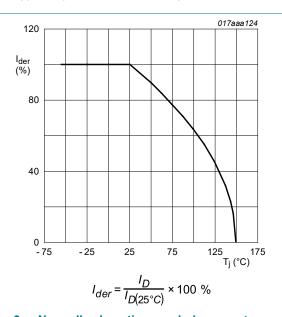


Fig. 3. Normalized continuous drain current as a function of junction temperature

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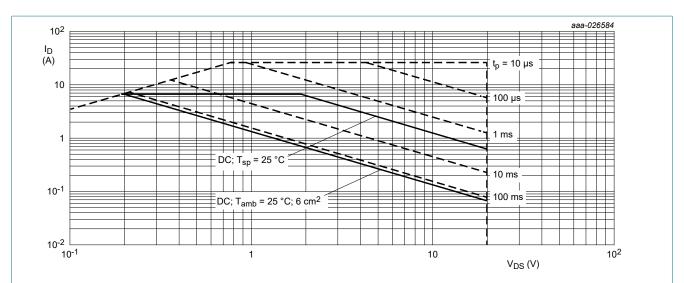


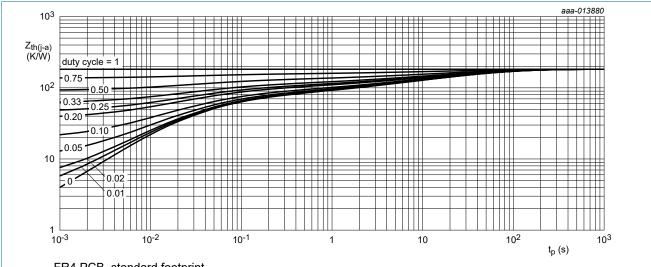
Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

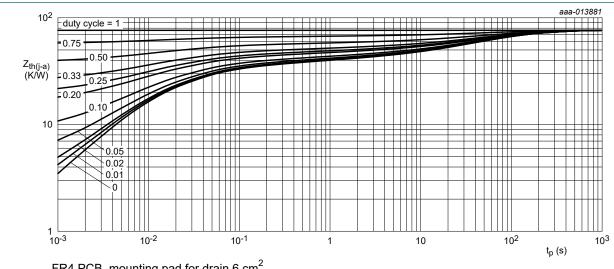
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from	in free air	[1]	-	180	225	K/W	
	junction to ambient	junction to ambient	[2]	-	65	85	K/W
		[3]	-	75	95	K/W	
	t ≤ 5 s	[3]	-	45	55	K/W	
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	5	10	K/W

- Device mounted on an FR4 Printed-Circuit Board (PCB), single sided-copper; tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain, 4 layer, 1 cm2
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm<sup>2</sup>

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

# PMCM6501UNE

20 V, N-channel Trench MOSFET

# 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.4	0.6	0.9	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
		V <sub>GS</sub> = 2.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	200	nA
		V <sub>GS</sub> = -2.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-200	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 3 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	17	21	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 3 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	25	29	mΩ
	$V_{GS} = 2.5 \text{ V}; I_D = 3 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	20	25	mΩ	
	V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 2 A; T <sub>j</sub> = 25 °C	-	22	32	mΩ	
		V <sub>GS</sub> = 1.5 V; I <sub>D</sub> = 1 A; T <sub>j</sub> = 25 °C	-	30	45	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS} = 5 \text{ V}; I_D = 3 \text{ A}; T_j = 25 \text{ °C}$	-	40	-	S
$R_G$	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	-	1.2	-	Ω
Dynamic ch	naracteristics		'			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = 10 \text{ V}; I_D = 3 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	19	28	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.2	-	nC
$Q_{GD}$	gate-drain charge		-	5.8	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	1050	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	190	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	180	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 6.6 A; V <sub>GS</sub> = 4.5 V;	-	7.3	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	28	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	100	-	ns
t <sub>f</sub>	fall time		-	46	-	ns
Source-drai	in diode		'	<u> </u>	'	'
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 1.2 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	0.6	1.2	V

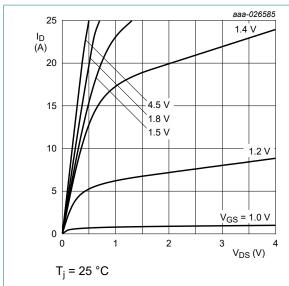


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

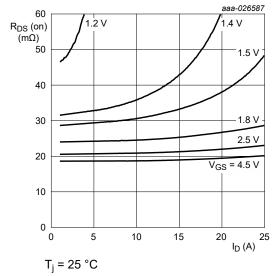


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

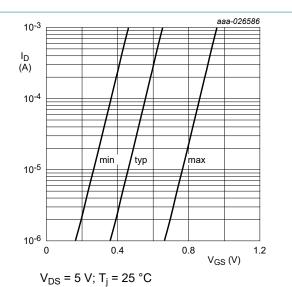


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

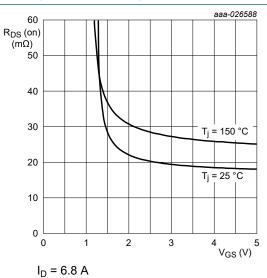


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

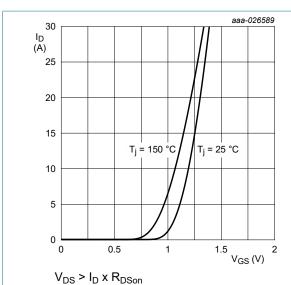


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

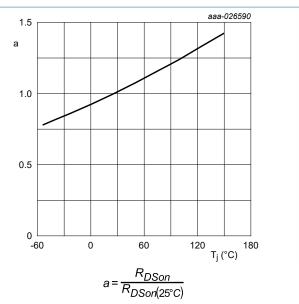


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

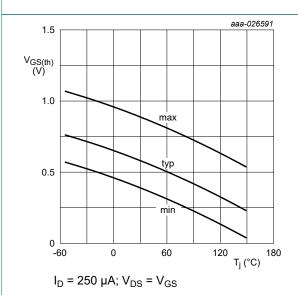
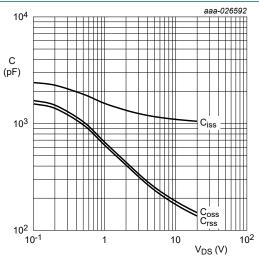


Fig. 13. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

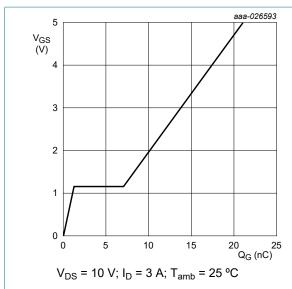


Fig. 15. Gate-source voltage as a function of gate charge; typical values

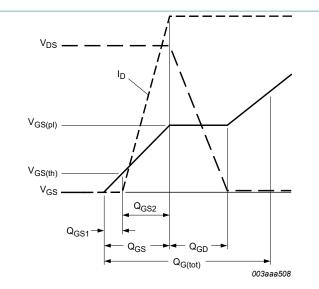


Fig. 16. Gate charge waveform definitions

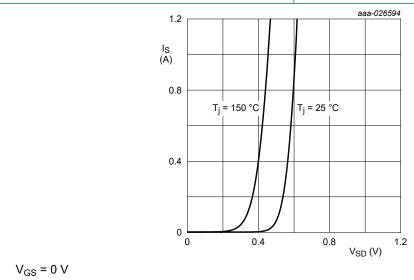
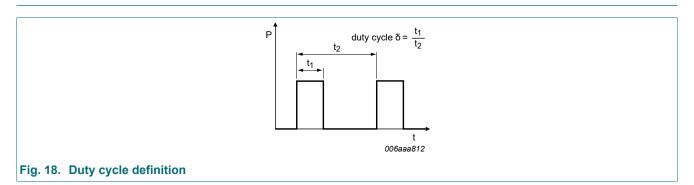
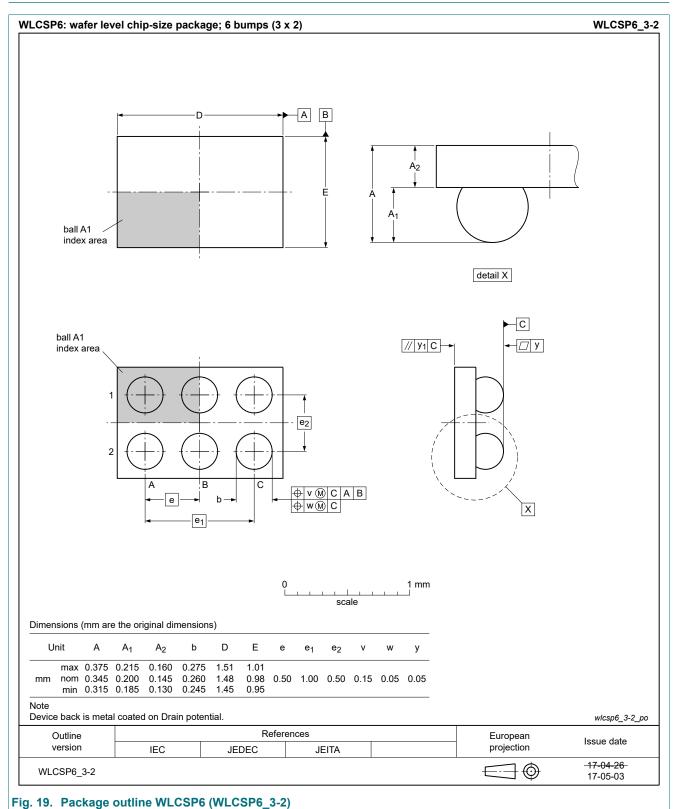


Fig. 17. Source current as a function of source-drain voltage; typical values

### 11. Test information

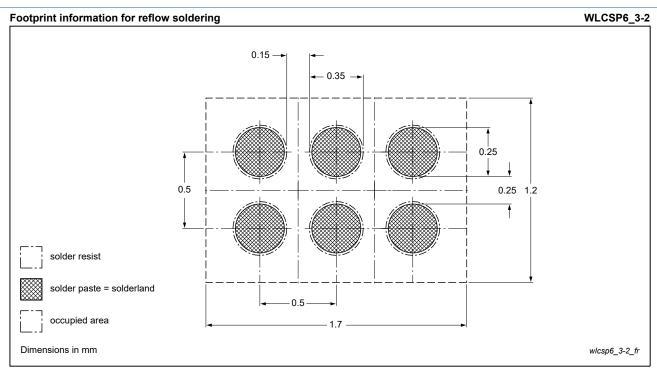


# 12. Package outline



1 1g. 15. 1 ackage outilile 11 2001 0 (11 2001 0\_5-2)

# 13. Soldering



# PMCM6501UNE

20 V, N-channel Trench MOSFET

# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMCM6501UNE v.2	20230602	Product data sheet	-	PMCM6501UNE v.1		
Modifications:	Chapter "Characteristics": typo correction for typical values of C <sub>iss</sub> , C <sub>oss</sub> and C <sub>rss</sub>					
PMCM6501UNE v.1	20170530	Product data sheet	-	-		

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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### Nexperia

# PMCM6501UNE

20 V, N-channel Trench MOSFET

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 2 June 2023

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